## **REMARKS**

1	Election/Restriction
2	The election of Group I, claims 1 - 10 is affirmed.
3	<u>Title</u>
4	The title has been changed.
5	<u>Drawings</u>
6 7	The objection to the drawings under 37 CFR 1.83(a) is respectfully traversed.
8	Claims 3 and 5 have been cancelled, thus rendering the objection moot.
9	Claim Rejections 35 USC 112
10	The rejection of claims 1 - 10 under 35 USC 112 is respectfully traversed

Claim 1 has been amended to specify that the barrier layer is between the 1 monocrystalline substrate and the buried strap. 2 Claim Rejections - 35 USC 102 3 The rejection of claims 1 - 7, 9 and 10 under 35 USC 102(b) is respectfully 4 traversed. 5 Claim 1 has been amended to recite explicitly that the barrier layer is Si-C. 6 The specification states in paragraph 23 that the term means that Si-O 7 bonds in the silicon surface are replaced with Si - C bonds. 8 Claim 1 has been further amended, in order to distinguish clearly over the 9 reference, to specify that the structure of the barrier layer is not that of 10 silicon carbide. 11 In contrast, the Tsunashima reference specifies in Col. 2, lines 56 - 57 that 12 the interface layer is silicon carbide. 13 Thus, there is a clear distinction between the invention defined by claim 1 14 and that of the reference. 15

1	In addition, claim 1 further specifies that the Si-C barrier layer has been
2	formed in the course of a plasma-assisted etch of an oxide layer. This last
3	restriction is in the nature of a product by process limitation that has
4	resulted in the novel structure specified earlier in the claim.
. 5	Claim Rejection 35 USC 103
6	The rejection of claim 8 under 35 USC 103 is respectfully traversed for the
<b>.</b> 7	same reasons as the rejection under 35 USC 102.
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8	For the foregoing reasons, allowance of the claims is respectfully
9	solicited.
10 11	Respectfully submitted,
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